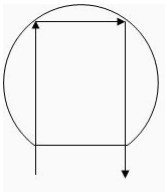
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Overall Thickness	250.00 +/- 4.50 µm	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<2.00µm	Guaranteed by Process
	6.0	Bow	<40.00µm	ADE to ASTM F534, 20%
	7.0	Warp	<40.00µm	ADE to ASTM F657, 20%
HandleSilicon	8.0	Handle Growth Method	CZ	Wafer Vendor
	9.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	10.0	Handle Thickness	250.00 +/- 4.50 µm	ADE, 100%
	11.0	Handle Doping Type	N	Wafer Vendor
	12.0	Handle Dopant	Phosphorous	Wafer Vendor
	13.0	Handle Resistivity	1-10 Ohmcm	Wafer Vendor
	14.0	Backside Finish	Polished with lasermarking - unique laser mark as per SEMI M12 (last 4 digits unique)	Wafer Vendor
DeviceSilicon	15.0	LPD Count	<30.00pces	@0.3um, Tencor 6220 particle counter
	16.0	Scratches	0	Bright Light, 100% (note 2)
	17.0	Haze	none	Bright Light, 100% (note 2)

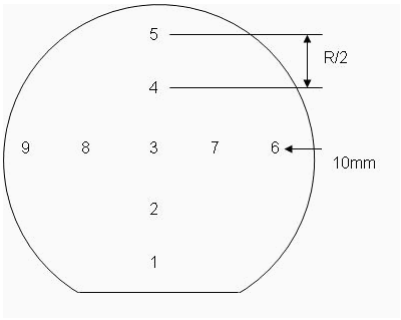
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information